

# RT3JGGM

Composite Transistor  
For high speed switching  
Silicon P-channel MOSFET

## DESCRIPTION

RT3JGGM is a composite transistor built with two INJ0103AX chips in SC-88 package.

## FEATURE

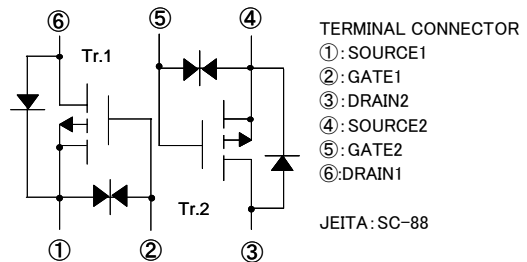
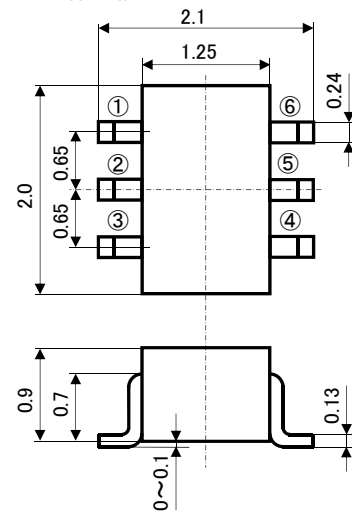
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage  $-1.8V$
- Low on Resistance.  
 $R_{DS(ON)}=0.67\ \Omega$  (TYP) @ $I_D=-400mA$ ,  $V_{GS}=-4.5V$   
 $R_{DS(ON)}=1.1\ \Omega$  (TYP) @ $I_D=-300mA$ ,  $V_{GS}=-2.5V$   
 $R_{DS(ON)}=1.6\ \Omega$  (TYP) @ $I_D=-10mA$ ,  $V_{GS}=-1.8V$
- High speed switching.
- Small package for easy mounting.

## APPLICATION

High speed switching , Analog switching

## OUTLINE DRAWING

Unit:mm



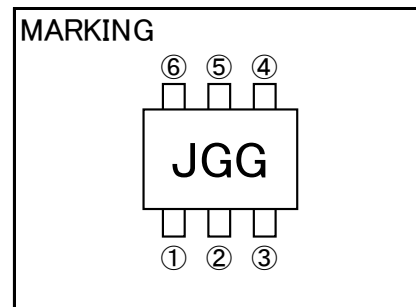
## MAXIMUM RATING ( $T_a=25^\circ C$ ) (Tr1,Tr2 Common)

SYMBOL	PARAMETER	RATING	UNIT
$V_{DSS}$	Drain-source voltage	-20	V
$V_{GSS}$	Gate-source voltage	$\pm 8$	V
$I_D$	Drain current(DC)	-550	mA
$I_{DP}$	Drain current(Pulse)	$-2.2^{*1}$	A
$P_D$	Total power dissipation	150	mW
		$600^{*2}$	mW
$T_{ch}$	Channel temperature	+150	$^\circ C$
$T_{stg}$	Range of Storage temperature	$-55 \sim +150$	$^\circ C$

\*1:  $P_w \leq 10\ \mu s$ , Duty cycle  $\leq 1\%$

\*2: Package mounted on glass-epoxy substrate  
( $20mm \times 20mm \times 1mm$ , Cu pad  $100mm^2$ )

## MARKING



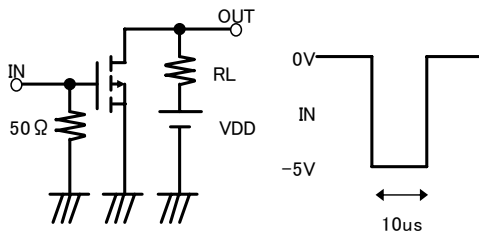
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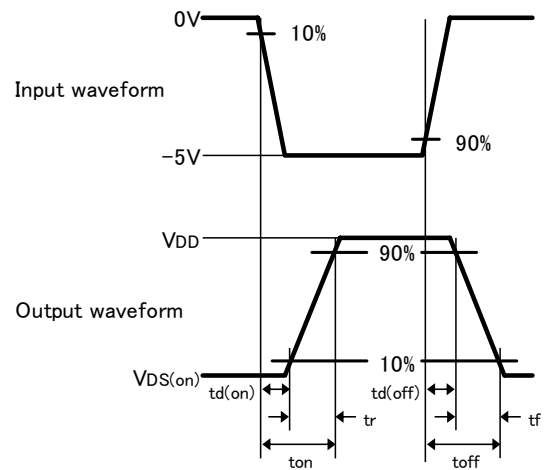
## ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1,Tr2 Common)

SYMBOL	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V(BR)DSS	Drain-source breakdown voltage	$I_D = -100\mu A, V_{GS} = 0V$	-20	-	-	V
I <sub>GSS</sub>	Gate-source leak current	$V_{GS} = \pm 5V, V_{DS} = 0V$	-	-	$\pm 0.5$	$\mu A$
I <sub>DSS</sub>	Zero gate voltage drain current	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1.0	$\mu A$
V <sub>th</sub>	Gate threshold voltage	$I_D = -250\mu A, V_{DS} = V_{GS}$	-0.6	-	-1.2	V
Y <sub>fs</sub>	Forward transfer admittance	$V_{DS} = -5V, I_D = -200mA$	-	560	-	mS
R <sub>DS(ON)</sub>	Static drain-source on-state resistance	$I_D = -400mA, V_{GS} = -4.5V$	-	0.67	-	$\Omega$
		$I_D = -300mA, V_{GS} = -2.5V$	-	1.1	-	
		$I_D = -10mA, V_{GS} = -1.8V$	-	1.6	-	
C <sub>iss</sub>	Input capacitance	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$	-	57	-	pF
C <sub>oss</sub>	Output capacitance		-	20	-	pF
t <sub>on</sub>	Switching time	$V_{DD} = -10V, I_D = -400mA$ $V_{GS} = 0 \sim -5V$	-	42	-	ns
T <sub>off</sub>			-	140	-	

### Switching time test condition



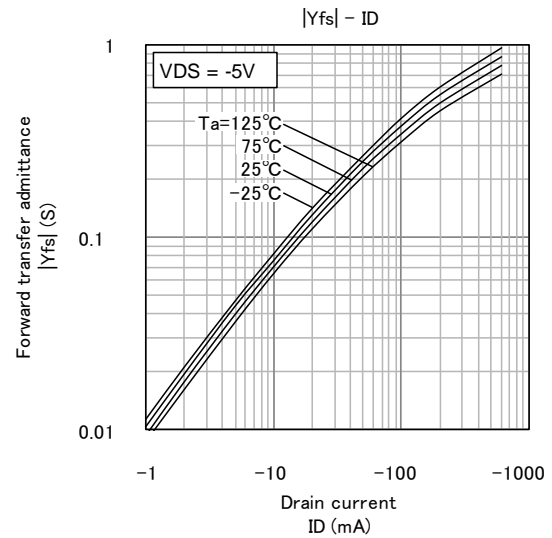
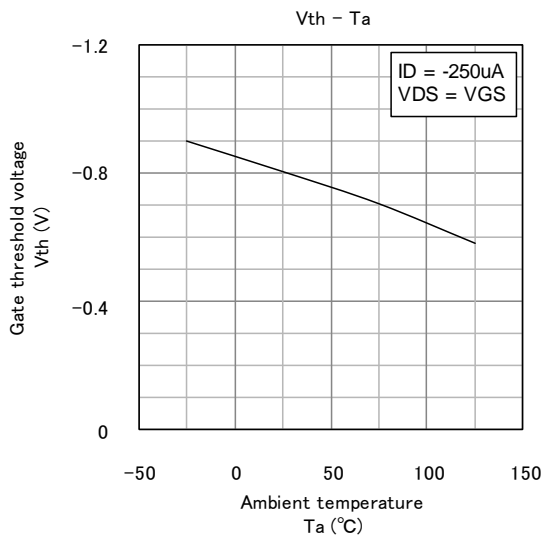
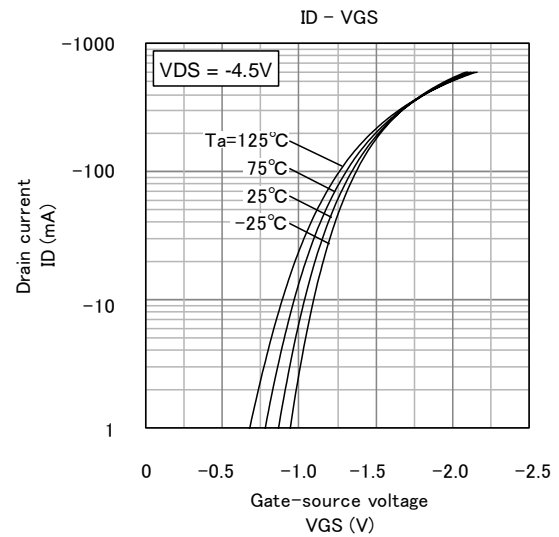
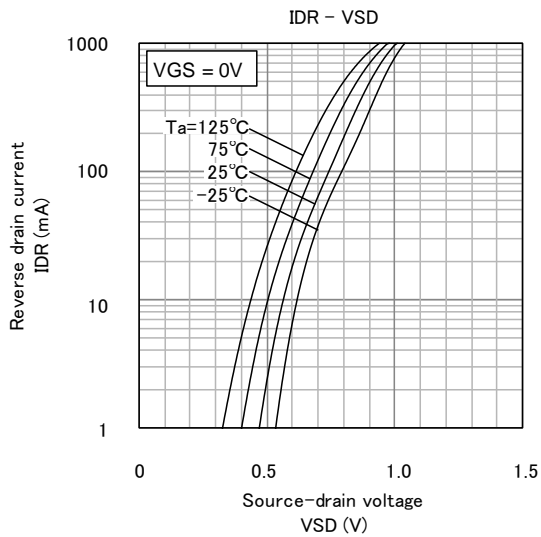
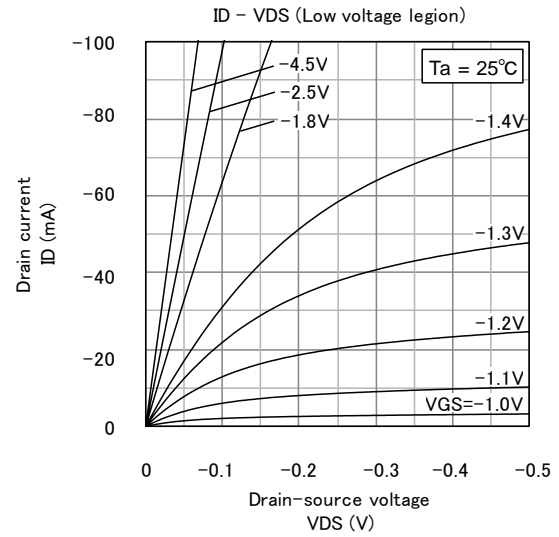
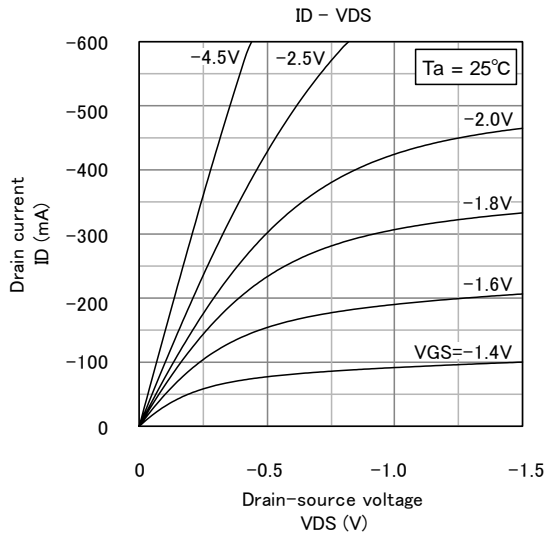
Duty  $\leq$  1%  
Input: tr, tf < 10ns  
VDD = -10V  
Common source  
Ta = 25°C



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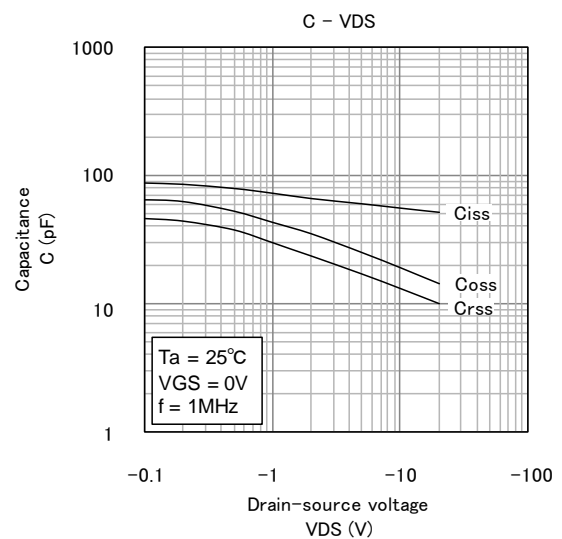
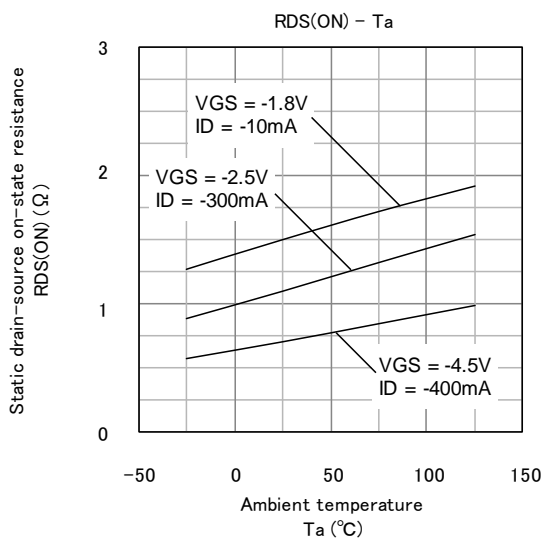
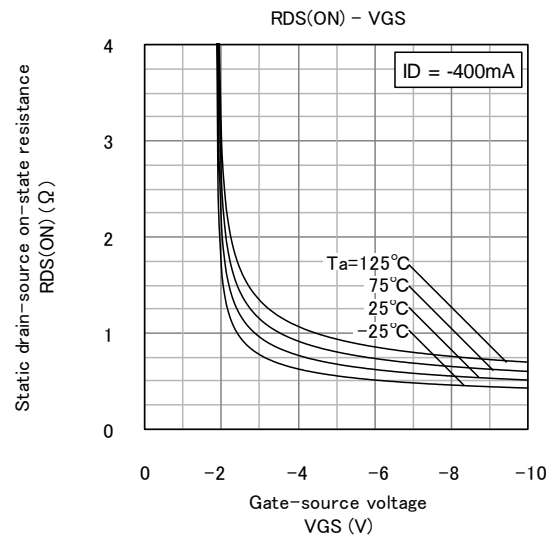
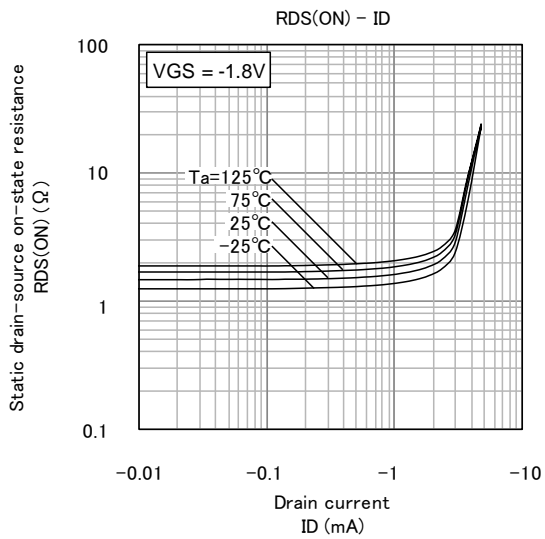
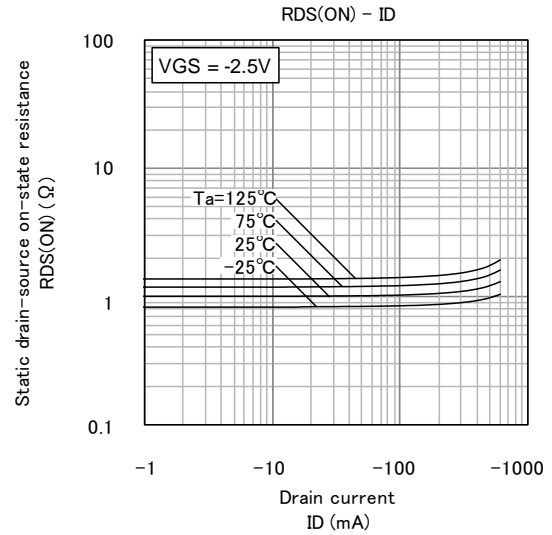
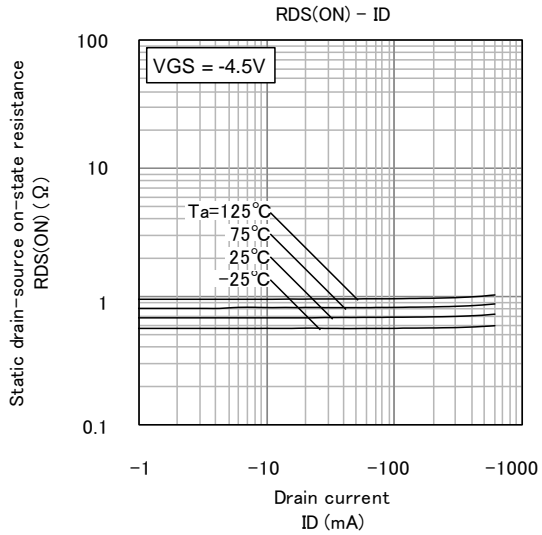
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## TYPICAL CHARACTERISTICS



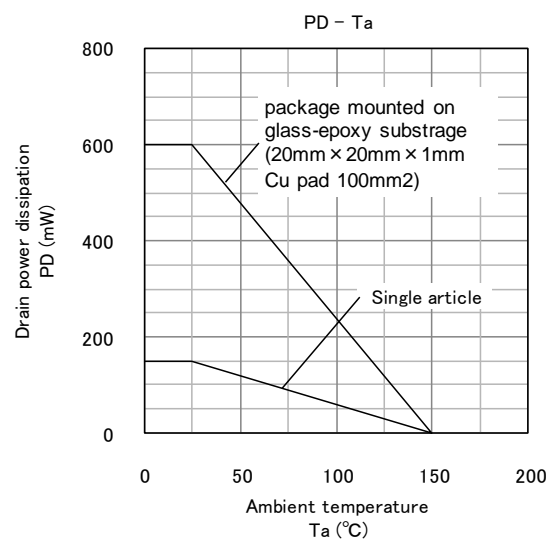
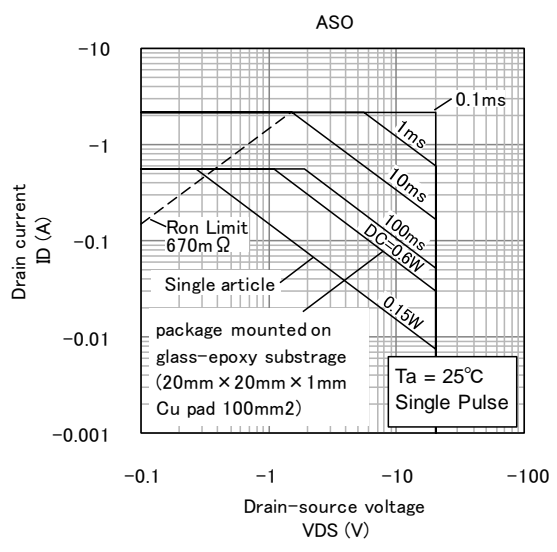
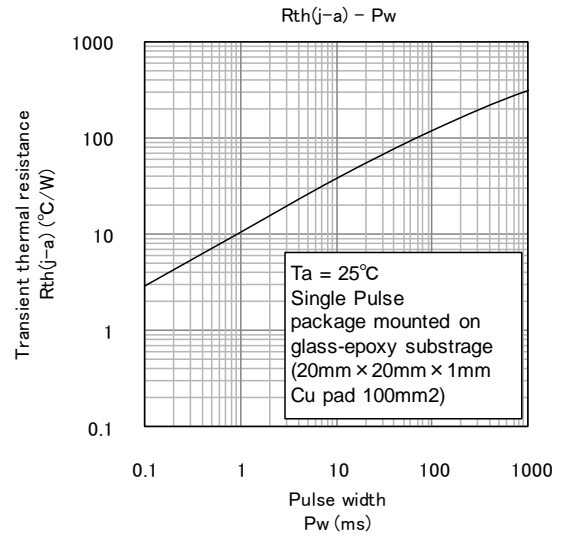
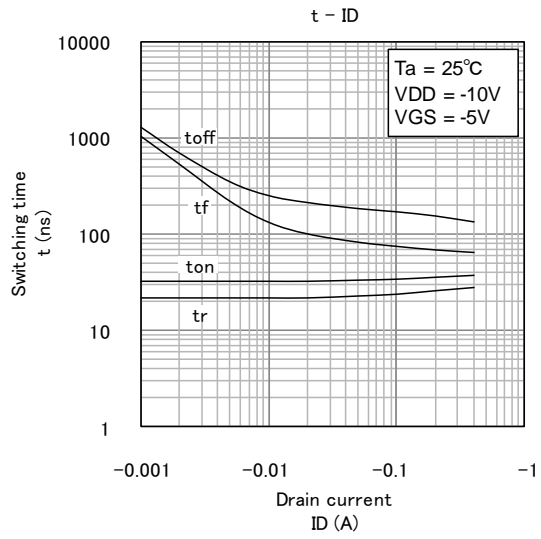
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